

UF601**Power MOSFET**

0.185A, 600V N-CHANNEL
DEPLETION-MODE POWER
MOSFET

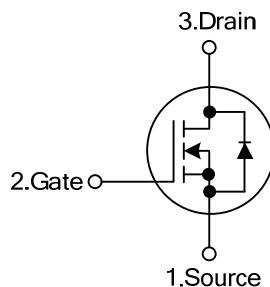
■ DESCRIPTION

The UTC **UF601** is an N-channel power MOSFET using UTC's advanced technology to provide the customers with high switching speed.

■ FEATURES

- * $R_{DS(ON)}=700\Omega$ @ $V_{GS}=0V, I_D=3mA$
- * High Switching Speed

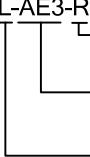
■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UF601L-AE3-R	UF601G-AE3-R	SOT-23	S	G	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

UF601L-AE3-R 	(1)Packing Type (2)Package Type (3)Lead Free	(1) R: Tape Reel (2) AE3: SOT-23 (3) G: Halogen Free, L: Lead Free
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■ ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage (Note 2)		V_{DSS}	600	V
Drain-Gate Voltage (Note 2)		V_{DGX}	600	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	Continuous	I_D	0.185	A
	Pulsed	I_{DM}	0.740	A
Power Dissipation		P_D	0.50	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55~+150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. $T_J=+25^\circ\text{C}\sim+150^\circ\text{C}$

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	250	$^\circ\text{C/W}$

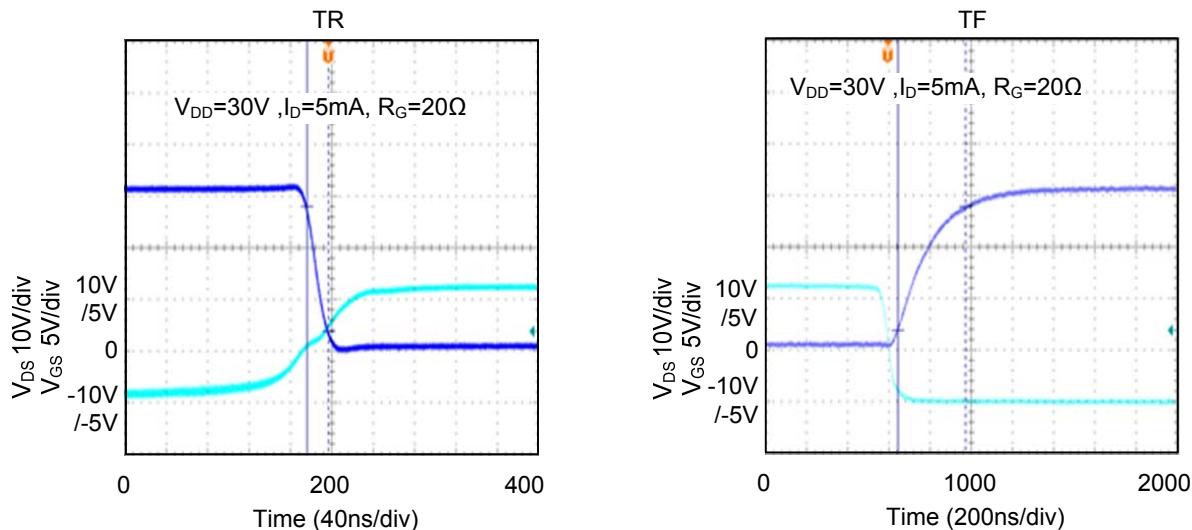
■ ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}, V_{GS}=-5\text{V}$	600			V
Drain-Source Leakage Current	$I_{D(OFF)}$	$V_{DS}=600\text{V}, V_{GS}=-5\text{V}$			0.1	μA
Gate-Source Leakage Current	Forward	I_{GSS}	$V_{GS}=+20\text{V}, V_{DS}=0\text{V}$		+100	nA
	Reverse		$V_{GS}=-20\text{V}, V_{DS}=0\text{V}$		-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=3\text{V}, I_D=8\mu\text{A}$	-2.7		-1.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=25\text{V}, V_{GS}=0\text{V}$	7.0			mA
Static Drain-Source On-State Resistance	$R_{DS(\text{ON})}$	$V_{GS}=0\text{V}, I_D=3\text{mA}$		600	700	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{GS}=0\text{V}, V_{DS}=25\text{V}, f=1.0\text{MHz}$		9.44		pF
Output Capacitance	C_{OSS}			2.28		pF
Reverse Transfer Capacitance	C_{RSS}			1.42		pF
SWITCHING PARAMETERS						
Total Gate Charge	Q_G	$V_{GS}=-5\sim 5\text{V}, V_{DS}=30\text{V}, I_D=5\text{mA}$		1.29		nC
Gate to Source Charge	Q_{GS}			0.1		nC
Gate to Drain Charge	Q_{GD}			0.47		nC
Turn-ON Delay Time	$t_{D(\text{ON})}$	$V_{GS}=-5\sim 5\text{V}, V_{DD}=30\text{V}, I_D=5\text{mA}, R_G=20\Omega$		4		ns
Rise Time	t_R			9		ns
Turn-OFF Delay Time	$t_{D(\text{OFF})}$			14		ns
Fall-Time	t_F			84		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage	V_{SD}	$I_{SD}=3.0\text{mA}, V_{GS}=-10\text{V}$			1.4	V

Notes: 1. Repetitive rating, pulse width limited by maximum junction temperature.

2. Pulse width $\leq 380\mu\text{s}$; duty cycle $\leq 2\%$.

- TYPICAL CHARACTERISTICS



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